

## CLAIMS

1. A process for producing a sintered aluminum nitride  
furnished with via holes, comprising providing an aluminum  
5 nitride molding having through-holes for via hole formation  
and through-holes for formation of dummy via holes not used  
for electrical connection, filling the through-holes for  
via hole formation and the through-holes for dummy via hole  
formation with a conductive paste and firing the aluminum  
10 nitride molding and conductive paste,

wherein the aluminum nitride molding is furnished with  
the through-holes for via hole formation and the  
through-holes for dummy via hole formation so that the  
through-holes for via hole formation having been filled with  
15 the conductive paste and the aluminum nitride molding  
respectively exhibit a firing shrinkage factor ( $X_v$ , %) and  
a firing shrinkage factor ( $X_s$ , %) whose difference,  $X_v -$   
 $X_s$ , is in the range of -1.0 to 9.5%.

20 2. A process for producing a sintered aluminum nitride  
furnished with via holes, comprising providing an aluminum  
nitride molding having through-holes for via hole formation  
and through-holes for formation of dummy via holes not used  
for electrical connection, filling the through-holes for  
25 via hole formation and the through-holes for dummy via hole

formation with a conductive paste and firing the aluminum nitride molding and conductive paste,

wherein at least one of the through-holes for via hole formation is in such a highly isolated state that,

5 therearound, other through-holes for via hole formation are not densely present, and wherein at least one of the through-holes for dummy via hole formation is formed around the through-hole for via hole formation of said highly isolated state.

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3. The process as claimed in claim 2, wherein, within a radius of 5.0 mm from a center of the through-hole for via hole formation of said highly isolated state, there are other through-holes for via hole formation whose volumes sum into  
15 0.9% or less of a whole volume within the radius.

4. The process as claimed in claim 3, wherein, within a radius of 5.0 mm from a center of the through-hole for via hole formation of said highly isolated state, through-holes  
20 for dummy via hole formation and other through-holes for via hole formation are formed so that their volumes sum into 1 to 6% of a whole volume within the radius.

508A<sub>31</sub> 5. The process as claimed in any of claims 1 to 4, wherein through-holes for dummy via hole formation are formed in a scrap zone within the sintered aluminum nitride.

5 6. The process as claimed in claim 5, wherein, after the firing, the scrap zone is cut off from the sintered aluminum nitride.

508A<sub>32</sub> 10 7. The process as claimed in any of claims 1 to 6, wherein a composition comprising 100 parts by weight of a refractory metal, 2 to 10 parts by weight of powdery aluminum nitride and 2 to 9 parts by weight of an organic vehicle is used as the conductive paste.

15 8. The process as claimed in claim 7, wherein the aluminum nitride molding, after the filling of the through-holes for via hole formation and through-holes for dummy via hole formation with the conductive paste, is dewaxed so that the aluminum nitride molding exhibits an internal residual  
20 carbon ratio of 800 to 3000 ppm, then fired at 1200 to 1700°C and further fired at 1800 to 1950°C.

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